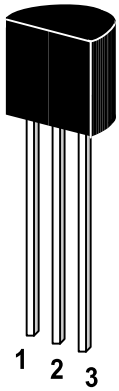
ST 2SC2668

NPN Silicon Epitaxial Planar Transistor
High frequency amplifier applications.

The transistor is subdivided into three groups, R, O and Y, according to its DC current gain.

On special request, these transistors can be manufactured in different pin configurations.



1. Emitter 2. Collector 3. Base

TO-92 Plastic Package
Weight approx. 0.19g

Absolute Maximum Ratings (Ta=25 °C)

	Symbol	Value	Unit
Collector Base Voltage	V_{CBO}	40	V
Collector Emitter Voltage	V_{CEO}	30	V
Emitter Base Voltage	V_{EBO}	4	V
Collector Current	I_C	20	mA
Base Current	I_B	4	mA
Power Dissipation	P_{tot}	100	mW
Junction Temperature Range	T_j	125	°C
Storage Temperature Range	T_S	-55 to +125	°C

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Characteristics at T_{amb}=25 ^{o}C

		Symbol	Min.	Typ.	Max.	Unit
DC Current Gain at V_{CE}=6V, I_C=1mA						
Current Gain Group	R	h_{FE}	40	-	80	-
	O	h_{FE}	70	-	140	-
	Y	h_{FE}	100	-	200	-
Collector Cutoff Current at V_{CB}=40V		I_{CBO}	-	-	0.5	μA
Emitter Cutoff Current at V_{EB}=4V		I_{EBO}	-	-	0.5	μA
Reverse Transfer Capacitance at V_{CE}=6V, f=1MHz		Cre	-	0.70	-	pF
Transition Frequency at V_{CE}=6V, I_C=1mA		f_T	-	550	-	MHz
Collector Base Time Constant at V_{CE}=6V, I_E=-1mA,f=30MHz		C_C·rbb'	-	-	30	ps
Noise Figure at V_{CC}=6V, f=100MHz, I_E=-1mA		NF	-	2.5	5.0	dB
Power Gain at V_{CC}=6V, f=100MHz, I_E=-1mA		G_{pe}	-	18	-	dB

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